

RT3J33M

Composite Transistor
For high speed switching
Silicon P-channel MOSFET

DESCRIPTION

RT3J33M is a composite transistor built with two INJ0003AX chips in SC-88 package.

FEATURE

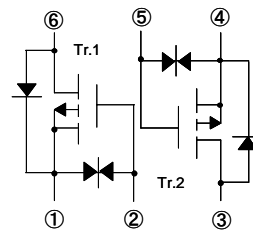
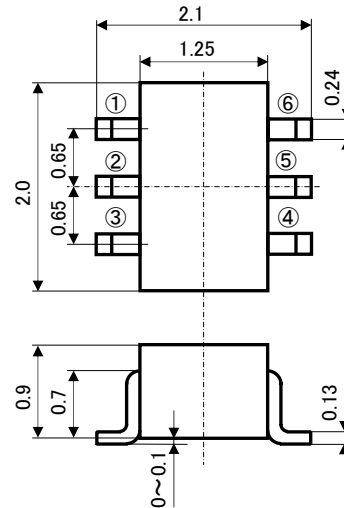
- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage is $-2.5V$
- Low on Resistance. $R_{ON}=2\Omega$ (TYP)
- High speed switching.
- Small package for easy mounting.

APPLICATION

High speed switching , Analog switching

OUTLINE DRAWING

Unit: mm



TERMINAL CONNECTOR

- ①: SOURCE1
- ②: GATE1
- ③: DRAIN2
- ④: SOURCE2
- ⑤: GATE2
- ⑥: DRAIN1

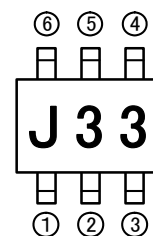
JEITA: SC-88

MAXIMUM RATING (Ta=25°C) (Tr1,Tr2 Common)

SYMBOL	PARAMETER	RATING	UNIT
V _{DSS}	Drain-source voltage	-20	V
V _{GSS}	Gate-source voltage	±8	V
I _D	Drain current(DC)	-200	mA
I _{DP}	Drain current(Pulse)	-400(※1)	mA
P _D	Total power dissipation	150	mW
T _{ch}	Channel temperature	+150	°C
T _{stg}	Range of Storage temperature	-55~+150	°C

※1: Pw ≤ 10μs, Duty cycle ≤ 1%

MARKING



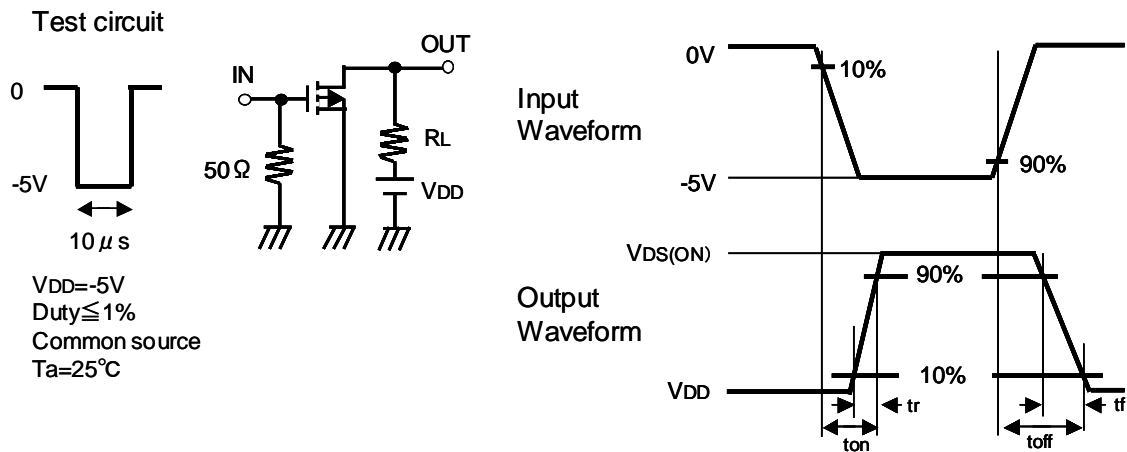
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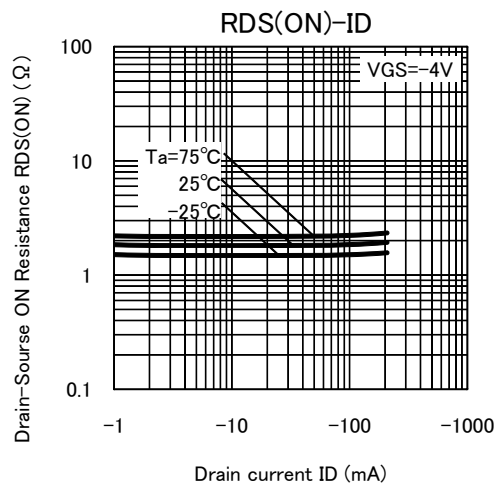
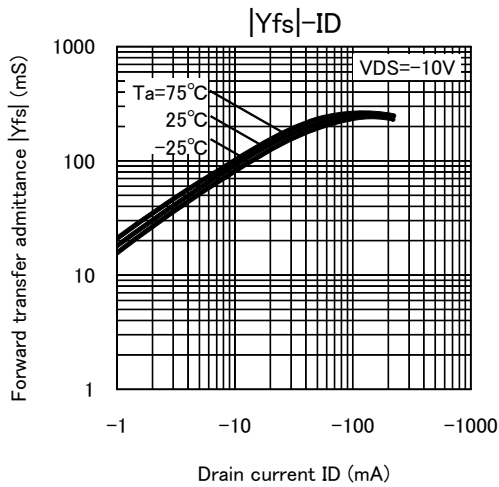
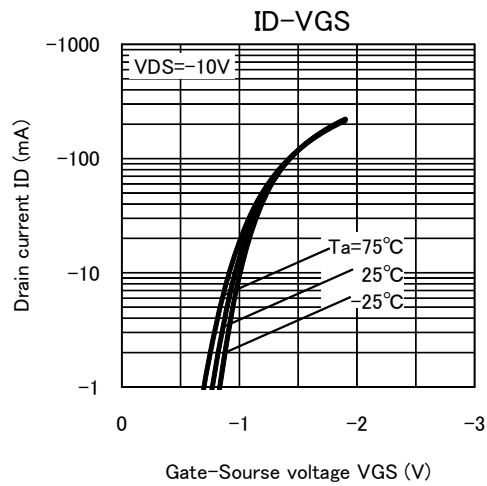
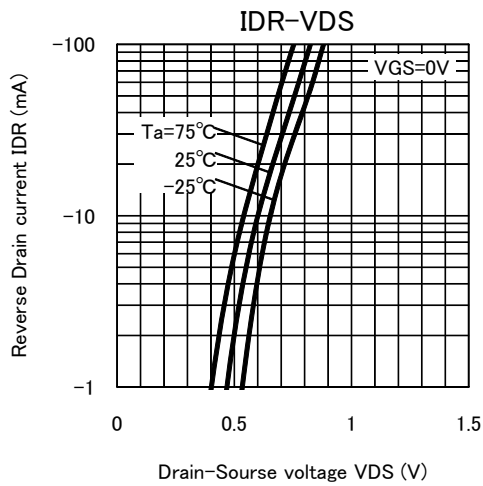
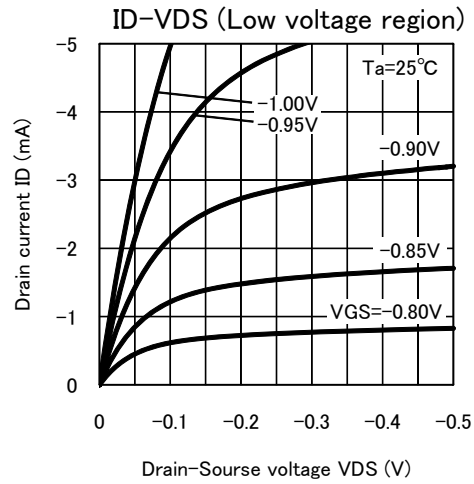
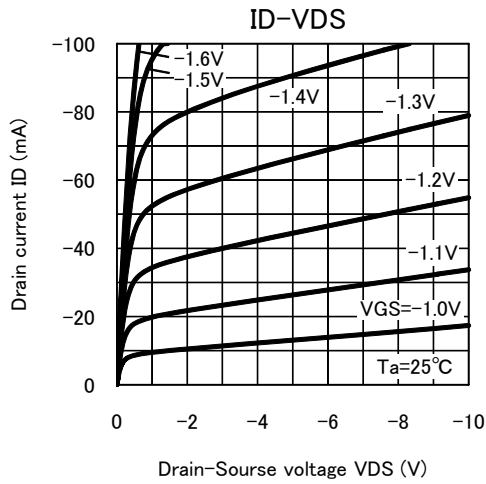
ELECTRICAL CHARACTERISTICS (Ta=25°C) (Tr1,Tr2 Common)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
			MIN	TYP	MAX	
V(BR)DSS	Drain-source breakdown voltage	ID=-100μA, VGS=0V	-20	-	-	V
IGSS	Gate-source leak current	VGS=±5V, VDS=0V	-	-	±0.5	μA
IDSS	Zero gate voltage drain current	VDS=-20V, VGS=0V	-	-	-1.0	μA
Vth	Gate threshold voltage	ID=-250μA, VDS=VGS	-0.6	-	-1.2	V
Yfs	Forward transfer admittance	VDS=-10V, ID=-0.1A	-	280	-	mS
RDS(ON)	Static drain-source on-state resistance	ID=-100mA, VGS=-4.0V	-	2.0	-	Ω
Ciss	Input capacitance	VDS=-10V, VGS=0V, f=1MHz	-	37	-	pF
Coss	Output capacitance		-	12	-	
ton	Switching time	VDD=-5V, ID=-10mA	-	16	-	ns
toff		VGS=0~-5V	-	110	-	

Switching time test condition

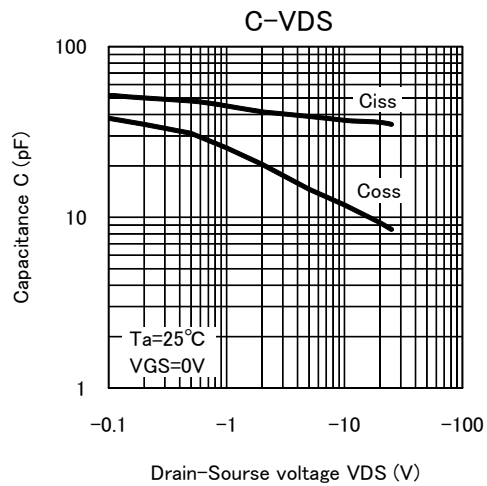
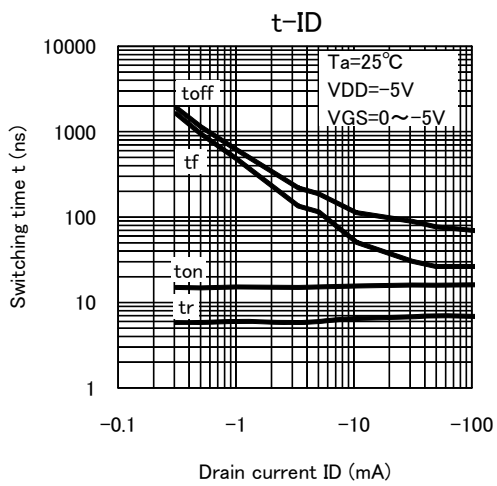
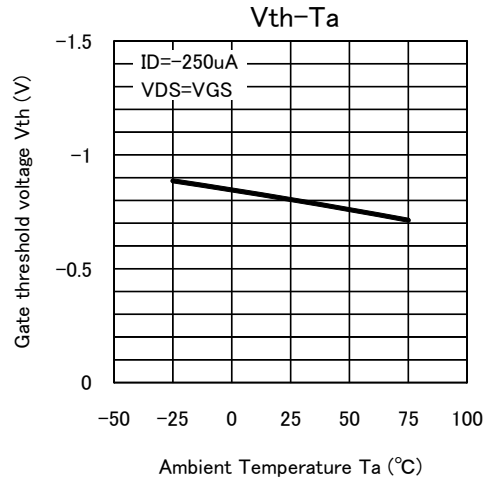
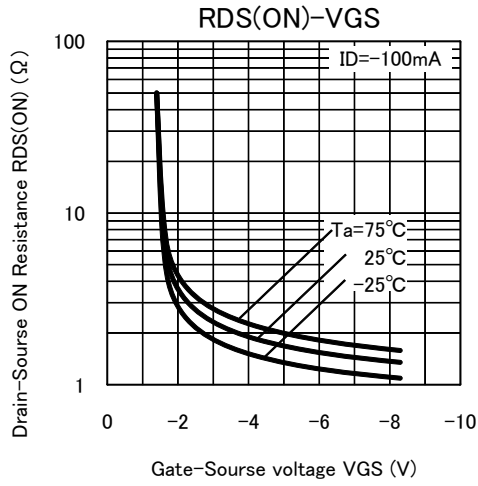


TYPICAL CHARACTERISTICS(Tr1,Tr2 Common)



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